

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

<b>Title of Invention</b>	PROCESS OPTIONS OF FORMING SILICIDED METAL GATES FOR ADVANCED CMOS DEVICES						
<p>Application Number :</p> <p>Confirmation Number:</p> <p>First Named Applicant: Ricky Amos</p> <p>Attorney Docket Number: FIS920020157US1</p> <p>Art Unit:</p> <p>Examiner:</p> <p>Search string: ( 5723893 or 6147388 or 6180501 or 6277719 or 6465312 ).pn</p>							
<b>US Patent Documents</b>							
<b>Note: Applicant is not required to submit a paper copy of cited US Patent Documents</b>							
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5723893	1998-03-03	YU, ET AL.			
	2	6147388	2000-11-14	MA, ET AL.			
	3	6180501	2001-01-30	PEY, ET AL.			
	4	6277719	2001-08-21	CHERN, ET AL.			
	5	6465312	2002-10-15	YU			
<b>Signature</b>							
Examiner Name				Date			